

The Role of National Nano Fab Center

- Advancing nanotechnology research, Education and commercialization in Korea

The 19th Korea-U.S Forum on Nanotechnology

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NNFC,
We Are Always Here for
Your Success

Contents

01 Who We Are

02 What We Have

03 What We Offer

04 Future Direction

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NANO 나노종합기술원
NATIONAL NANOFAB CENTER

Who We Are

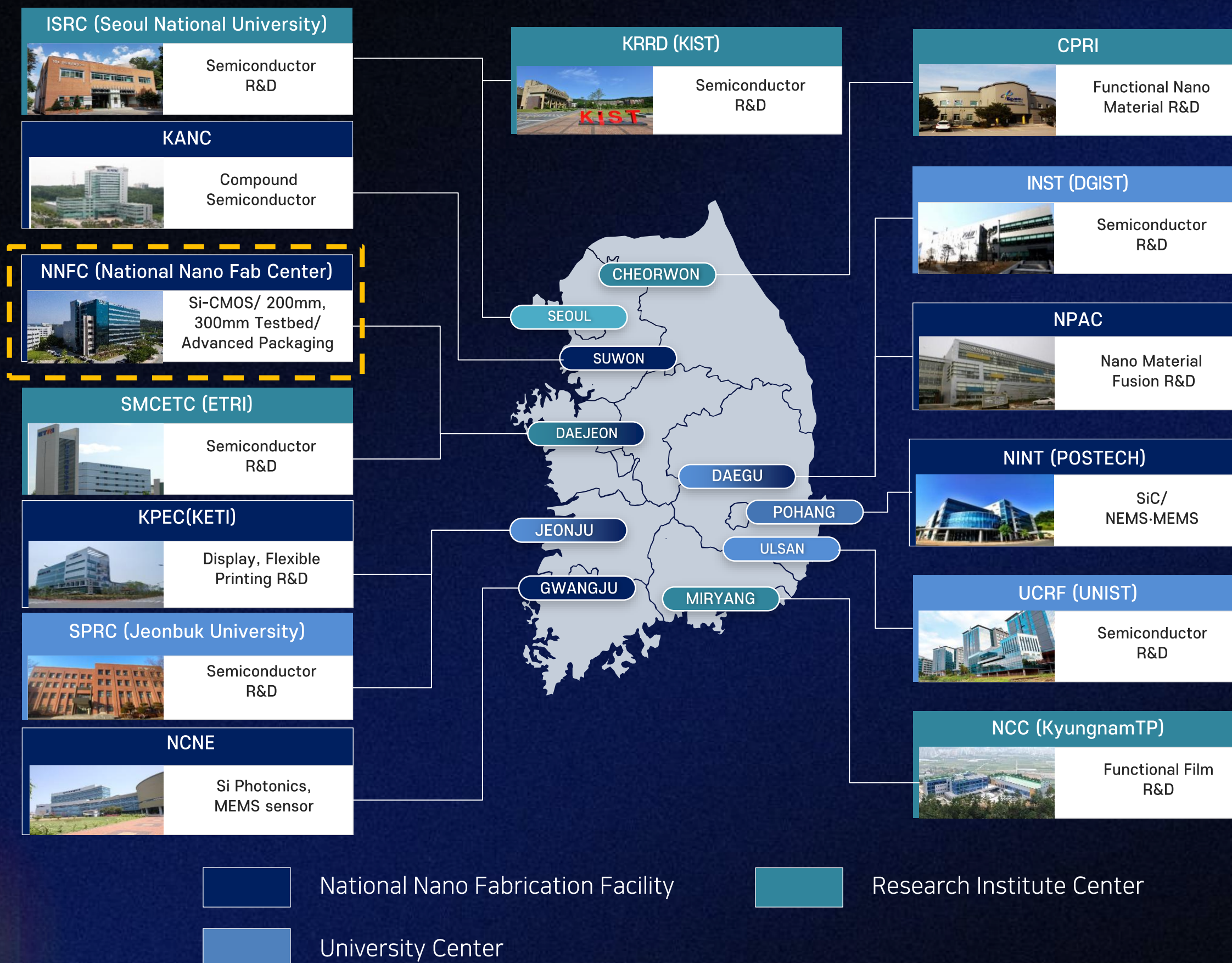
01

[Korea Infrastructure Organization for Nanotechnology]

01

"Who We Are"

Public and University Nanofabrication Facilities in Korea



01

"Who We Are"

National Nano Fab Center(NNFC)

- Basis of Establishment

. Nano Technology Development Promotion Act (Article 11, 2002)

- Established in 2004

. Affiliated with Korea Advanced Institute of Science and Technology

- Affiliated with the Ministry of Science and ICT in 2014

. Became a national R&D facility for advancing nanotechnology

- Expanded the testbed platform from 200mm to 300mm


. Invested in 12-inch Fab equipment investment (~50B ₩) in 2019

. Designated as Advanced Packaging Development Hub (~50B ₩) in 2024

- Collaboration with Top global R&D centers

. Joint technology MOU with NY CREATES (2024)

. Memorandum of Cooperation with imec (2025)

2002. 7	2004. 5	2014. 1	2019. 12	2021. 2	2024. 3	2024. 5
Establishment of the NNFC @ KAIST Campus	Affiliated Institution of KAIST	Inclusion under the Ministry of Science, Technology & ICT	Designation as N-Facility (in the Nano-Semiconductor Field)	Established 12inch Testbed for nano-semiconductor	Signed the Joint Technology Collaboration MOU with NY Creates(USA)	NNFC celebration of 20 th anniversary & international forum
						

01

"Who We Are"

National Nano Fab Center(NNFC)

Enabling Act

Article 11 of Nano Technology Development
And Promotion Act(Korea)

Mission

"The Service Provider for Advancing Nanotechnology"

- ① Promoting the joint use of nano-facility between industry, academia, and institutes
- ② Fostering engineers & college students through training programs in cutting-edge facilities
- ③ Commercializing research outcomes & Supporting small and venture companies

Main Service Domain

- ❖ Testbed Service (8-inch 12-inch) and Logic CMOS Fabrication (0.18um 8-inch MPW)
- ❖ Nano-biosensor/chip fabrication
- ❖ Semiconductor and Display convergence technology platform
- ❖ MEMS sensor fabrication
- ❖ Analysis and measurement service
- ❖ Semiconductor-Micro Solid State Battery Interfacing Platform
- ❖ Silicon Quantum Device fabrication

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What We Have

02

NNFC's Facility

Total Area

26,446m²

Research Building

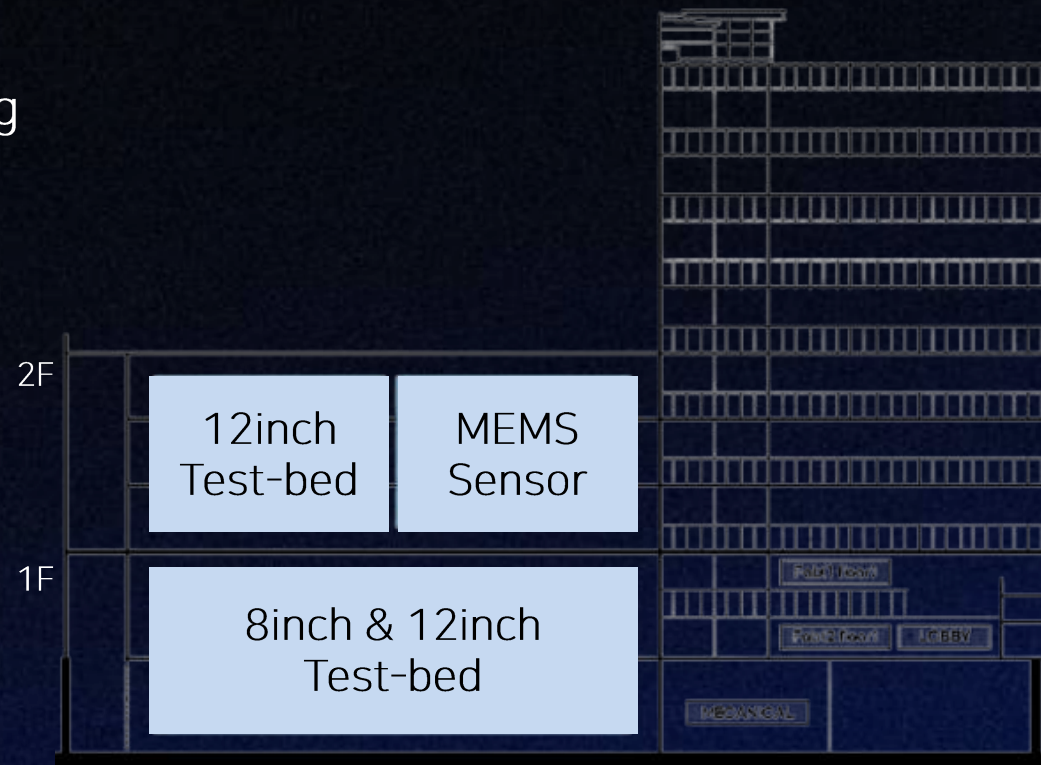
B1~ 9F(16,585m²)

Fab Building

2F(4,989m²)

Central Utility
Building

B1~ 4F(4,620m²)



Fab(1 floor)

2,500m²

Fab(2 floor)

2,500m²

Area

- 12-inch test-bed : 248m²
- 8-inch test-bed : 2,231m²

Area

- 12-inch test-bed : 992m²
- MEMS Sensor (8-inch) : 992m²

Equipment

8-inch

- Contact aligner, I-line stepper, KrF, ArF, E-beam patterning
- **ArF Dry Scanner** : Twinscan Dual-stage 70nm resolution(NA 0.85)
- Providing highly efficient processes through Mix & Match techniques

12-inch

- **ArF Immersion**(40nm for line & space) and its double patterning(20nm)
- Stitching for large area covering & its application ; Wire Grid Polarizer
- Hole patterning with only 1 mask(40 ~ 18 nm)

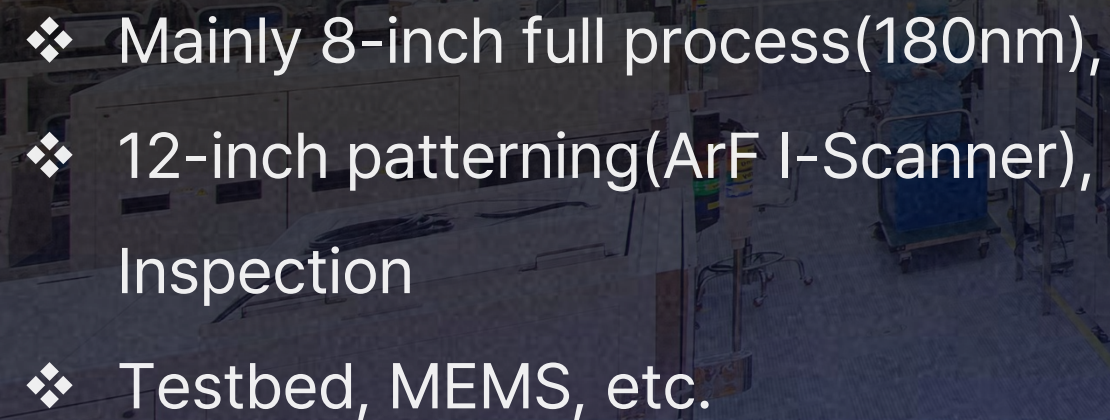
Semiconductor manufacturing service

- **Fully equipped 8-inch processes and partially equipped 12-inch processes**
- High quality support and collaboration by a well-experienced in-house experts
- Equipment open to use by qualified engineers from customers



"What We Have" – Fab Layout

'The First Floor'

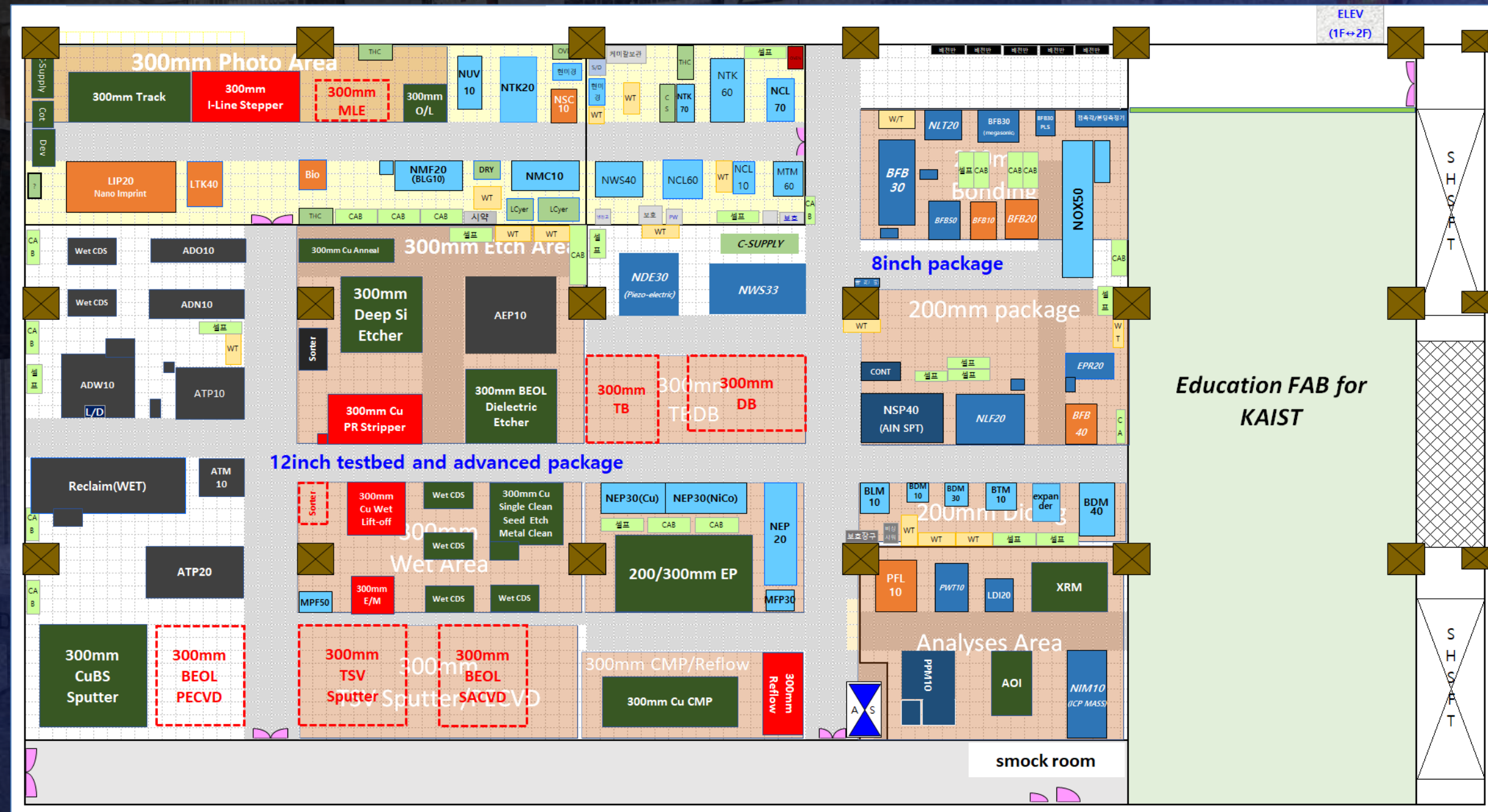
- 
- ❖ Mainly 8-inch full process(180nm),
 - ❖ 12-inch patterning(ArF I-Scanner),
Inspection
 - ❖ Testbed, MEMS, etc.



As of 30 June 2025

'The Second Floor'

- ❖ Testbed for 12-inch Equipment (Etch, Diffusion, T/F, etc.)
- ❖ 12-inch-based Advanced Packaging(in preparation)
- ❖ 8-inch-based Sensor



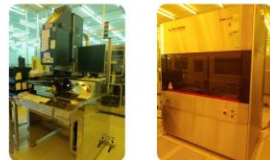
✓ Expansion to 12-inch advanced packaging by 2029

8-inch Semiconductor Manufacturing Service Total Equipment : 171 units

Photolithography & Etch

1x Lithography

- Contact Aligner (EV Group)
- Mask Generator (Heidelberg)



Contact Aligner, Mask Generator

4x(5x) Lithography

- ArF Scanner (ASML)
- KrF Scanner (ASML & Nikon)
- I-line Stepper (Nikon)



ArF Scanner, KrF Scanner, I-line Stepper

Metrology

- CD SEM (Hitachi)
- Overlay (KLA-Tencor)
- Particle Counter (KLA-Tencor)
- Defect Inspection (NEXTIN)



CD SEM, Overlay, Defect Inspection

Oxide Etcher

- Dielectric Etch
 - SiO₂, Si₃N₄, SiON...
 - HM, Spacer, Contact, SAC...
- PR Stripper
 - O₂ Plasma PR Strip



Dielectric Etcher [Lam Research, TEL]
PR Stripper [PSK]

Poly & Metal Etcher

- Poly Etcher
 - Si Substrate, Poly-Silicon Etch
- Metal Etch
 - Ti, TiN, Al, W, TaN
 - Ni, Au, Pt, W, Al...



Metal Etch System [Lam Research, AMAT]
Metal Etcher [Oxford]

DRIE

- DRIE (Deep Reactive Ion Etch)
 - Bosch Process, TSV Etch



Deep Si Etcher [Gigalane, SPTS]

Diffusion

Diffusion Furnace

- Wet Oxidation
- Dry Oxidation
- Forming Gas Anneal (H₂)
- High & Low Temp. Anneal



Furnace System [Centrotherm]

Ion Implantation & RTP

- High Energy Ion Implantation
- High Current Ion Implantation
- Medium Current Ion Implantation
- Spike Rapid Thermal Process
- Rapid Thermal Process



Ion Implantation & RTP [Axcelis, AMAT & Metron]

Cleaning Process

- Pre-metal Cleaning
 - HF, BOE, SC1, SPM, H₃PO₄...
- Post-metal Cleaning - Solvent...
- MEMS Wet Process
 - SC1, BOE, SPM, NH₄OH, KOH...



Wet Station [HIT]

Laser Anneal System

- Laser Source : Nd:YAG Green laser
- Wavelength : 532nm
- Max Pulse : 400mJ
- Pulse Stability : ±3%
- Beam Size : 5*5mm²



Laser Anneal System [DIT]

LP-CVD System

- LPCVD TEOS/Nitride
- LPCVD Poly-Si & a-Si
- LPCVD Doped Poly-Si (Ph3)
- LPCVD Low Stress Nitride



LP-CVD System [Centrotherm]

CMP System

- Oxide/Poly-Si CMP
- Cu Barrier & Seed Metal CMP
- W Barrier & Seed Metal CMP
- CMP Brush Cleaning / Chemical Cleaning



CMP System [Doosan DND & CTS]

Thin-film

Thin-Film @ PECVD

- PECVD
 - SiO₂, SiN, SiON
 - PE-TEOS
 - BPSG, PSG, BSG
 - a-Si, ACL (Amorphous Carbon Layer)



PECVD System [Lam Research, AMAT, TES]

Thin-Film @ Metal

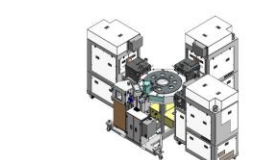
- Sputter
 - Al & Cu Metal Interconnection
 - Multi-Target Sputter & Evaporator
- Tungsten(W) CVD Plugging
- Electroplating - Cu, NiCo...



Sputter & W CVD [AMAT, Sorona, KVT]
Electroplating [EEJA]

Thin-Film @ ALD

- ALD (Atomic Layer Deposition)
 - High-k Materials
 - Al₂O₃, HfO₂, ZrO₂, TiO₂, Ta₂O₅
 - Dielectric : SiO₂ ...
 - Metal & Nitride : TiN ...



Multi-Chamber ALD System [CN1]

Sawing @ Package

- Stealth Laser Dicer
 - Only Si wafer ≤ Ø200mm
 - Dynamic focal point system
 - Completely dry process
- Blade Dicer : Si & Glass Saw



Stealth Laser & Blade Dicer [DISCO]

Die Separator

- Die Separator
 - DAF / UV Film applicable
 - Cooling Chamber : Min. -15°C
 - Heating Module : Max. 250 °C
 - 300mm wafer available



Die Separator [DISCO]

Multi-Chamber CVD

- PECVD
 - Multi Frequency TEOS USG
 - ACL(300°C, 400°C, 550°C)
- SACVD
 - BPSG, PSG, USG



Multi(PE & SA)CVD System [AMAT]

- 8-inch-based CMOS integrated device platform – 180nm Logic CMOS technology
- Unit, module, and integrated process services based on 180nm CMOS full process

12-inch Semiconductor Manufacturing Service Total Equipment : 21 units

Photolithography

ArF Immersion Scanner

TWINSCAN XT1900Gi @ ASML



- Single-Wafer Processing with In-Line Track
- 1.35-NA 193nm Projection Lens
 - Resolution down to 45nm(annular)
- Immersion Dual-Stage Technology
- AERIAL XP Polarized Illuminator
- 6-kHz ArF Laser Technology

Auto Track System

Lithius-Pro-i @ TEL



- 4 Loadports, Process coater / developer
- Immersion Top-coat Process
 - ITC & ITR (Top-Coat Coater & Remover)
- Develop Process (Alkali soluble)
- Wafer Rinse process (SRS & PIR)
 - SRS/PIR : Pre/Post Exposure Rinse

CD-SEM Thickness Measurement Defect Inspection

CG6300 @ Hitachi



Spectra FX 200 @ KLA



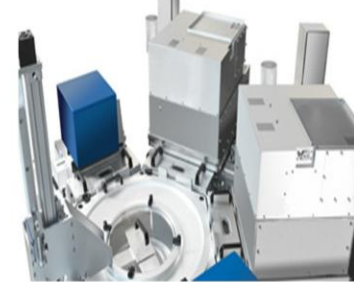
AEGIS @ NEXTIN



Dry Etch

Dry Etcher @ Oxide/Poly

2300e5 Platform Flex GX @ Lam Research



- 2 Loadports, TCP type plasma source
- Dielectric dry etch system
 - Low-k and ultra low-k dual damascene
 - Self-aligned contacts
 - Capacitor cell, Mask open
 - 3D NAND H/R hole, trench, contact

PR Stripper

SUPRA N @ PSK



- 3 Loadports, Single-Wafer Processing
- 2 PM with FCIP R3 Plasma source
 - High strip rate by ATM wafer heating
 - PR removal with low plasma damage
- End point detector with 309nm wavelength
- Process gas : O₂ / N₂ / H₂(4%)N₂

Diffusion/Thin-film /Wet Clean

Oxidation/LPCVD Furnace

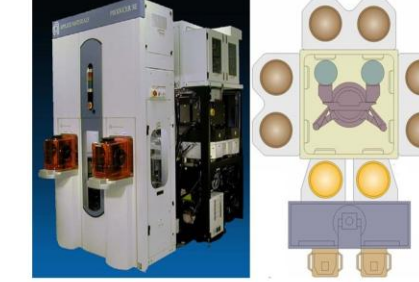
WIDAS @ WONIX IPS QUIXACE @ KEK



- 2 Loadports
- Batch Process (125ea Wafers/batch)
- 1 Tube / System
 - Oxidation System, LPCVD System
- Vertical Type Furnace
- Vacuum Load Lock Type (N₂ Purge)

Multi-Chamber PECVD

Producer SE System @ AMAT



- 2 Loadports, Single-Wafer Processing
- 3 Twin Process Chamber / 1 System
 - TEOS USG
 - SiH₄-Based SiO₂/SiN_x/SiON
 - Amorphous Carbon Layer
- RPS Clean

Single Wafer Cleaner

300mm Single Wafer Processor



- 2 Loadports, Single-Wafer Processing
- 2 Process Chamber / 1 System
 - 2 Dispensers/Chamber
 - Pre-Dep. Clean : DHF, SC-1
 - Post-Etch Clean : LAL15, DSP
 - IPA-DI/N₂ Spin Dryer

✓Pattern/Blanket Wafer Service

- Minimum Line/Space Pitch \geq 20nm half-pitch (using double patterning)
- Deposition of various thin/thick films(e.g. oxide, nitride, multiple layers etc.)

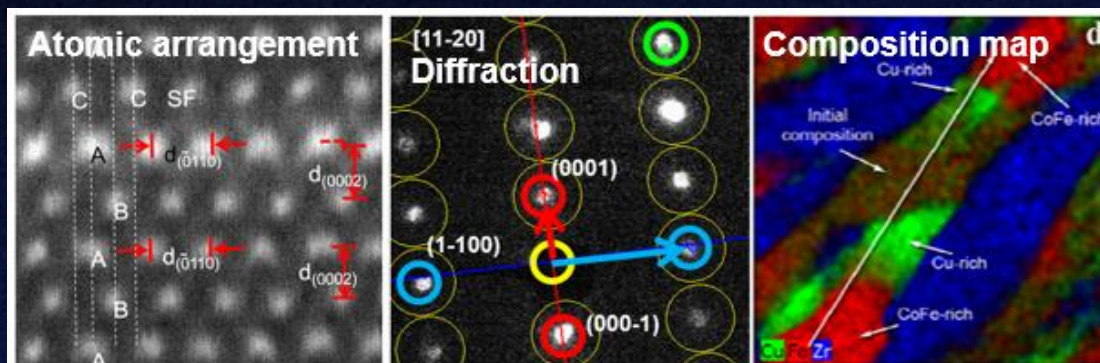
✓Testbed Service for Performance Assessment

- New materials(e.g. Photoresist etc.) , gas, slurry...
- Equipment parts/modules

Analysis “Deliver high-quality data with speed”

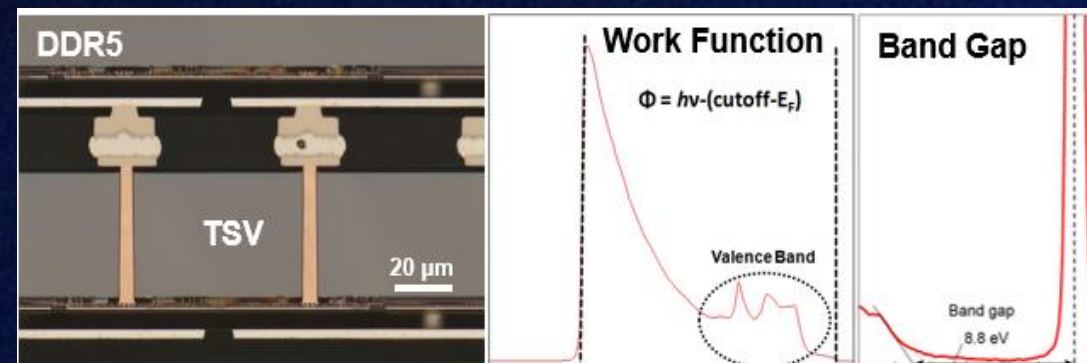
Structural Analysis

1. Atomic resolution
2. Microscopy (HRSTEM)
3. Crystallography (4D STEM)
4. Spectroscopy (EDS, EELS)
5. Cooling, heating, biasing and air-free



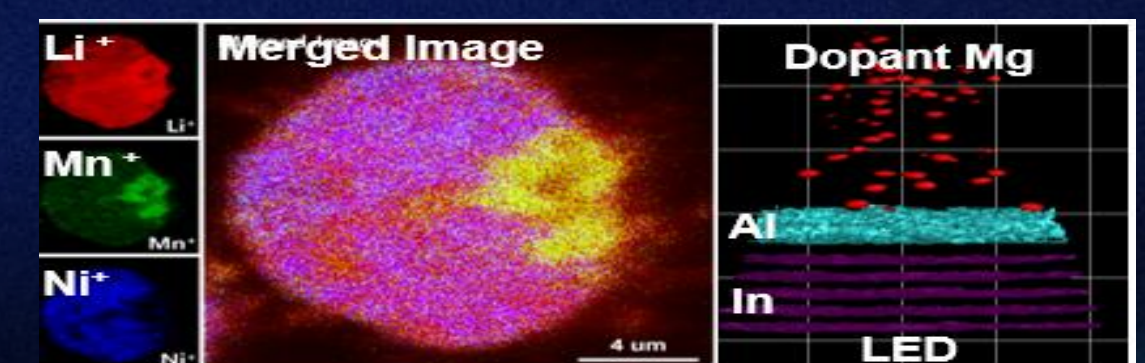
Product Analysis

1. Reverse engineering
2. Process analysis
3. Failure analysis
4. Intellectual property analysis
5. Electrical characterization



Surface Analysis

1. Composition analysis
2. Doping profile
3. 1D/2D/3D analysis
4. Electronic structure
5. Bonding structure



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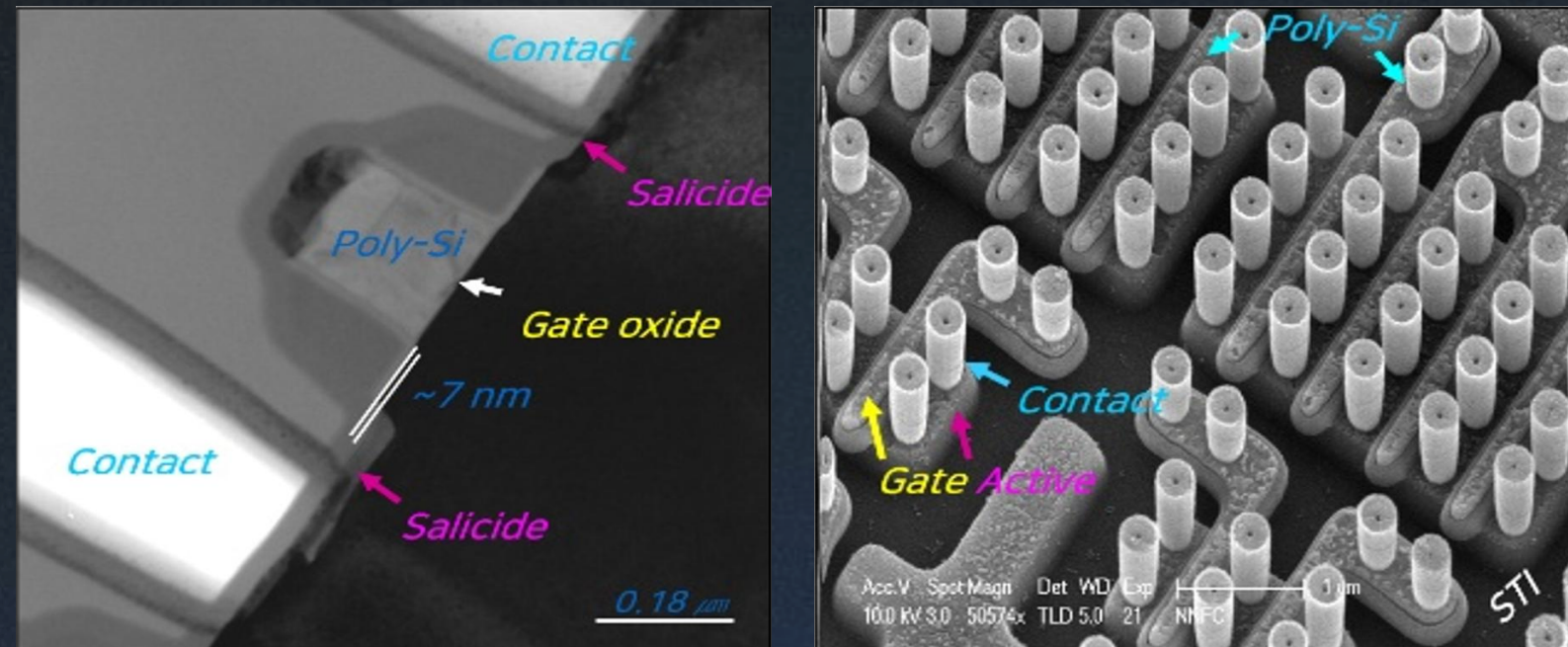
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What We Offer

03

03 "What We Offer"

8-inch CMOS Integrated Device Platform



NNFC's 180nm Standard CMOS Process

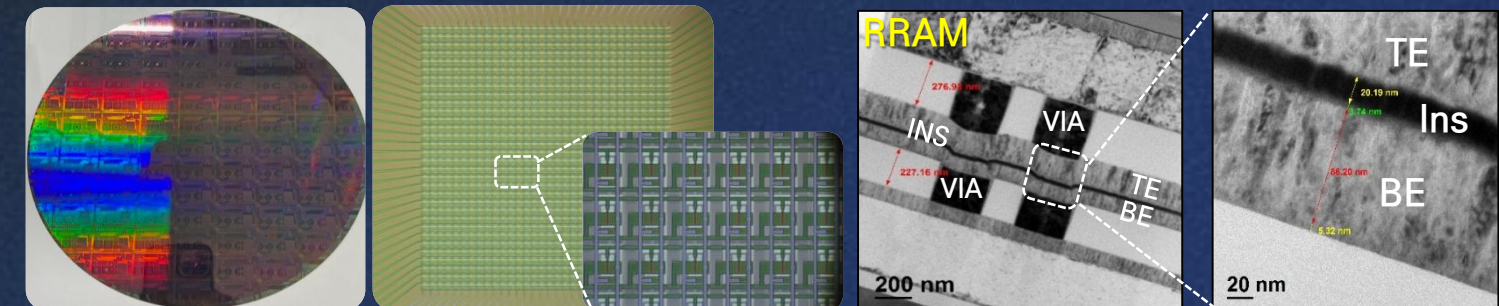
MPW support using 8-inch Platform

- Establishment and technical validation of an 8-inch, 180nm CMOS Integrated Device Platform via MPW
- NNFC is expanding 180nm CMOS design capabilities and advancing 130nm CMOS technologies

NNFC's 180nm
CMOS Standard Process

CMOS-compatible Specialized
Process for Intelligent Devices

NNFC's R&D Support for Intelligent Semiconductors



NNFC's Intelligent Device : 32 X 32 (1Kb) CMOS + RRAM (1T1R)

Support for Intelligent Semiconductor R&D

- Growing demand for R&D support for intelligent semiconductors
- Supporting commercialization through CMOS-based intelligent semiconductor libraries

03 "What We Offer"

12-inch Semiconductor Testbed Platform

Materials

Photoresist, Underlay, Etching Gas, etc.
- Process performance, Defects, Etch Resistance, Etch rate, etc.

ArF Immersion Photoresist

Parts

Board, Pump, Generator, Sensor, etc.
- Sensitivity, Reliability, Longevity Error verification, etc.


Demonstration of a process by-product suppression heater

Equipment


Etcher, Deposition, Analysis system, etc.
- Performance evaluation of prototype equipment

12-inch Deep Reactive Ion Etcher (DRIE)
Etch rate, Uniformity, Etch Profile, etc.


Energy, Focus Margin Evaluation



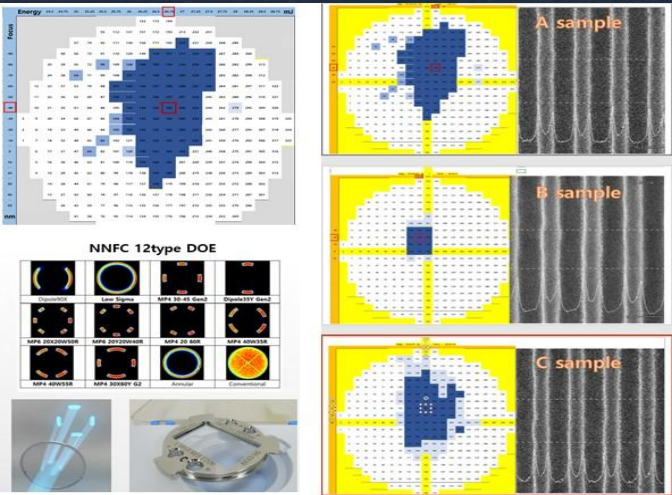
ArF immersion Scanner
ASML_XT1900Gi



Track
TEL_Lithus Pro i

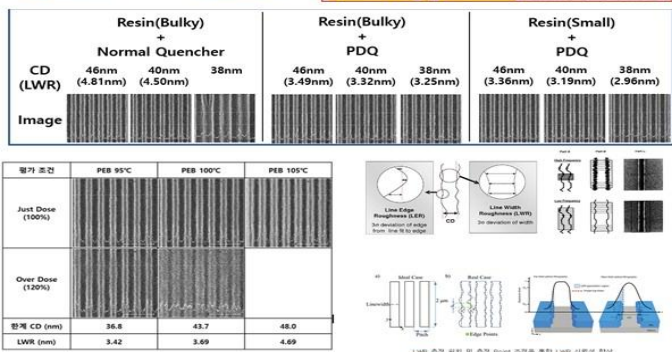


CD SEM
Hitach_CG6300

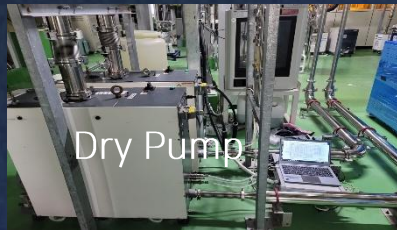


NNFC 12type DOE

Resin(Bulky)	Resin(Bulky)	Resin(Small)
Normal Quencher	PDQ	PDQ
46nm (4.81nm)	40nm (3.49nm)	46nm (3.36nm)
40nm (4.50nm)	38nm (3.32nm)	40nm (3.19nm)
38nm	38nm (3.25nm)	38nm (2.96nm)

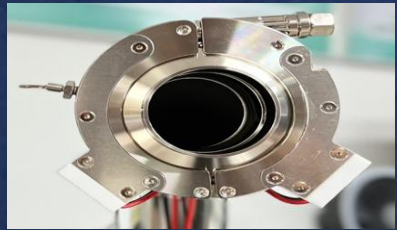


Dry pump exhaust section






Dry Pump

Carbon Film Clamp Heater



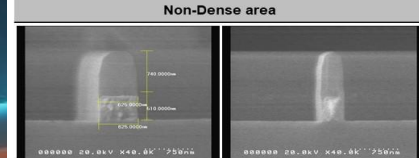
Before & after Clamp Heater

Etch depth, dense CD, Angle

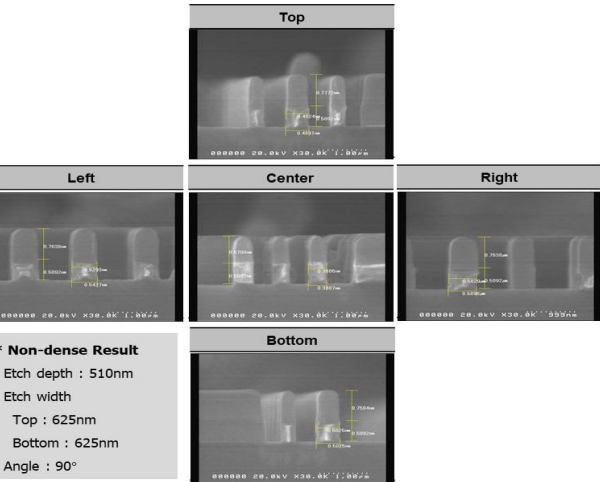
Position	Etch Depth	Etch Width		Angle
		Top	Bottom	
Top	510nm	482nm	489nm	89.6°
Center	510nm	388nm	388nm	89.9°
Bottom	510nm	502nm	502nm	90.0°
Left	510nm	529nm	542nm	89.2°
Right	510nm	582nm	589nm	89.6°
Average	510nm			89.7°
Angle UniF.				0.44%

Non-Dense area



* Non-dense Result

- Etch depth : 510nm
- Etch width
- Top : 625nm
- Bottom : 625nm
- Angle : 90°



Advanced Packaging

※ 12-inch-based Advanced Packaging is under preparation

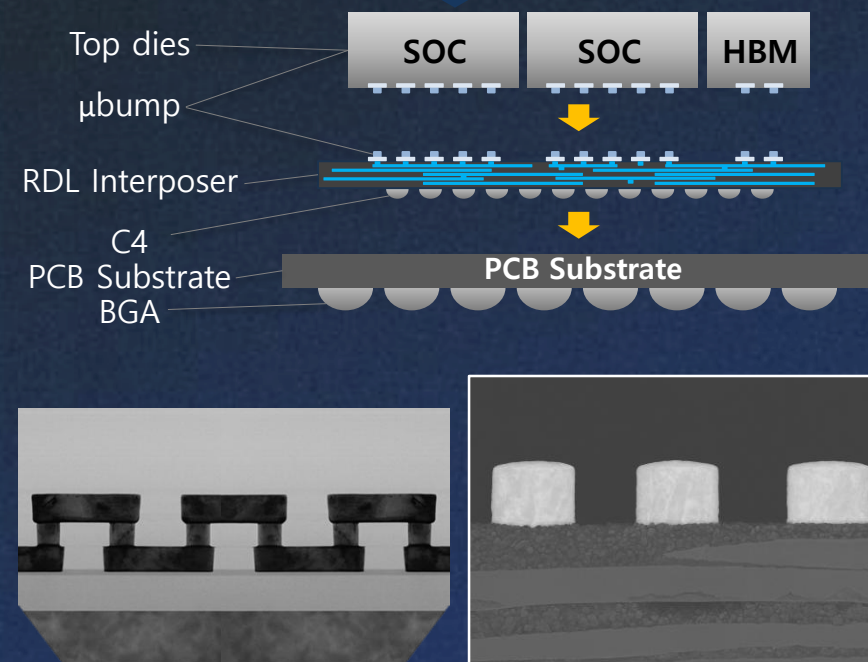
8-inch Heterogeneous Integration



Hetero Sub. PKG in NNFC

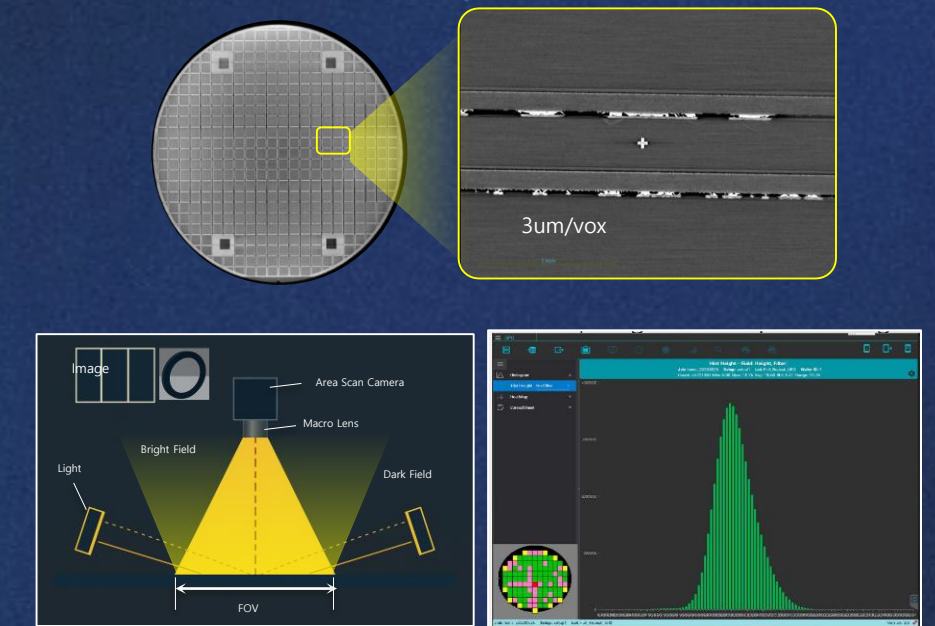
- Wafer bonding
- TSV & Cu damascene
- Thin wafer process
- Test & Inspection

8-inch Interposer



Inorganic Si Interposer

- RDL
- TSV
- BUMP
- Material Evaluation

Failure Analysis
(Destructive, Non-D)

Inspection & Metrology

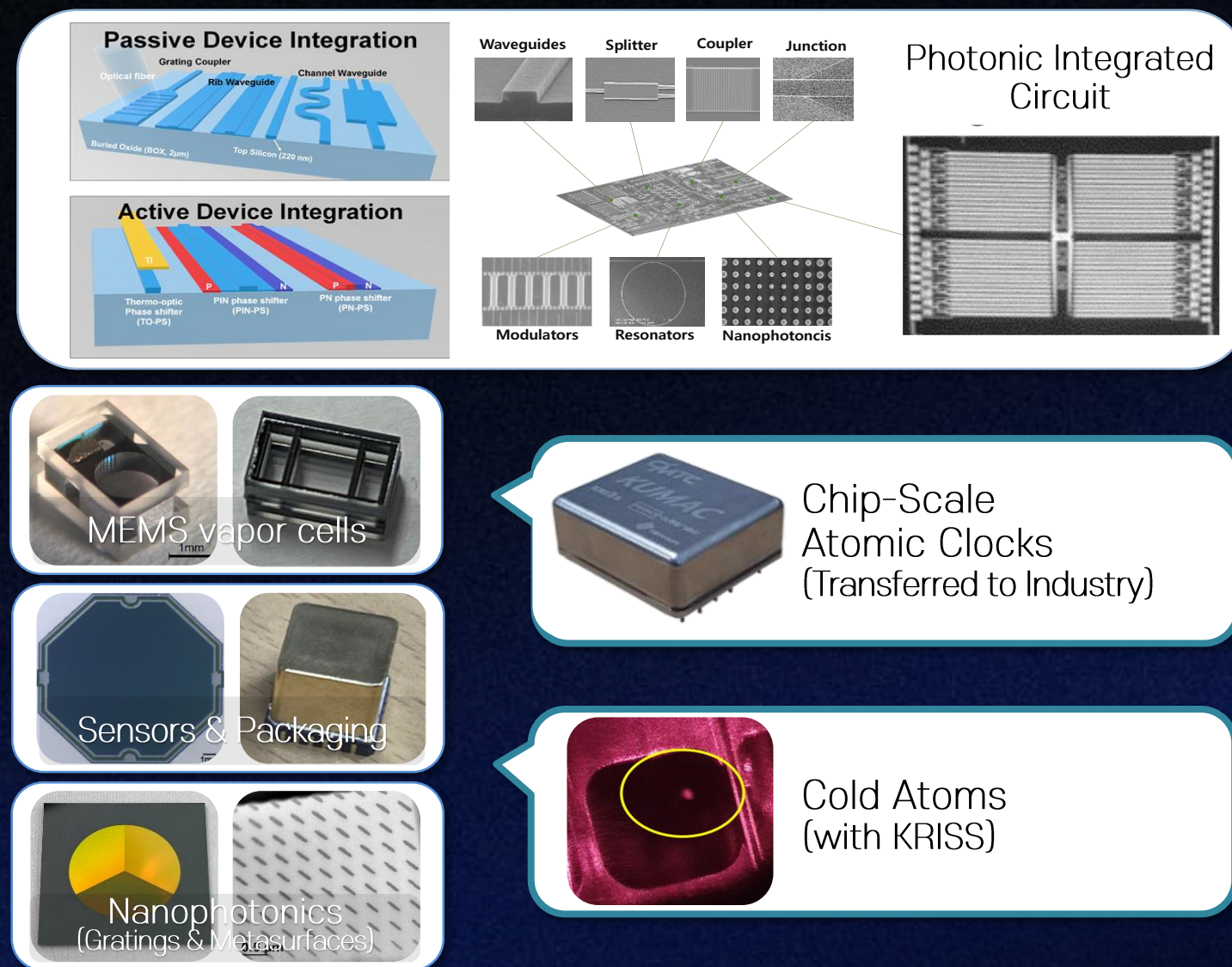
- X-ray Computed Tomography
- 3D non-destructive analysis
- Automated Optical Inspection
- TSV/Trench Depth
- Inner Crack Inspection

03

"What We Offer"

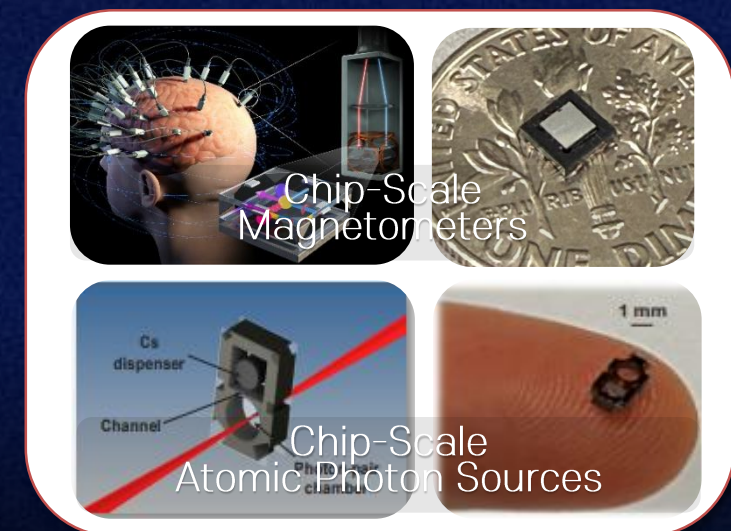
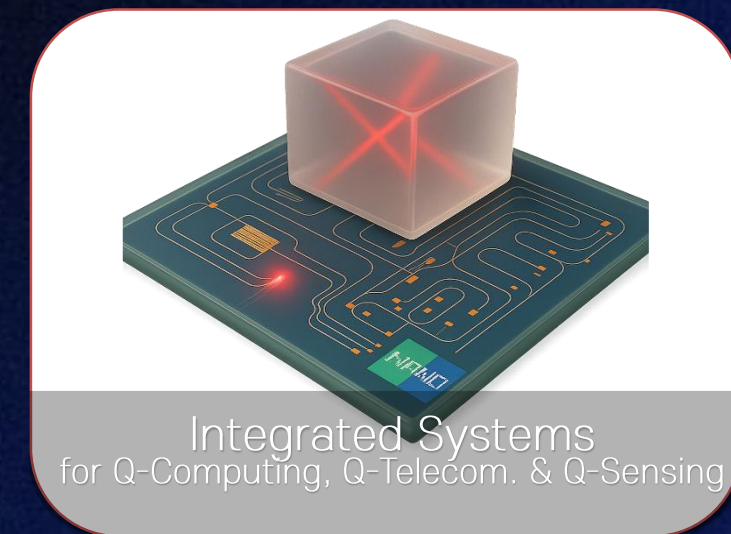
Quantum on Silicon Technology Platform

Quantum Technology Toolbox



Vertical Evolution (Integration)

Horizontal Evolution (Application Expansion)



Since 2014

Present

Future

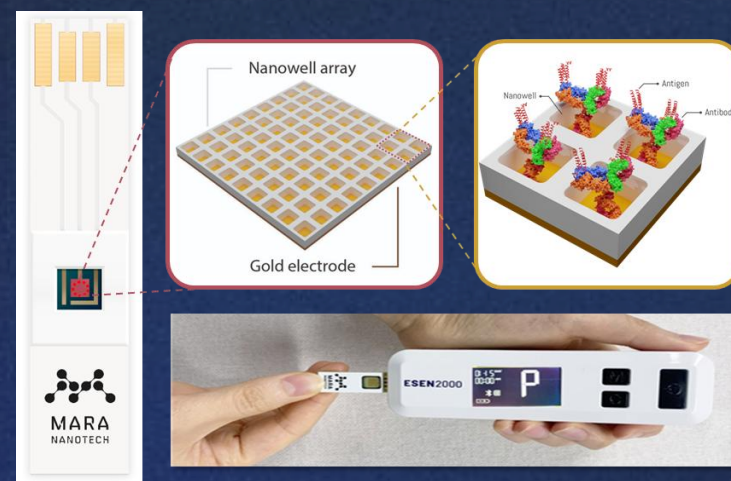
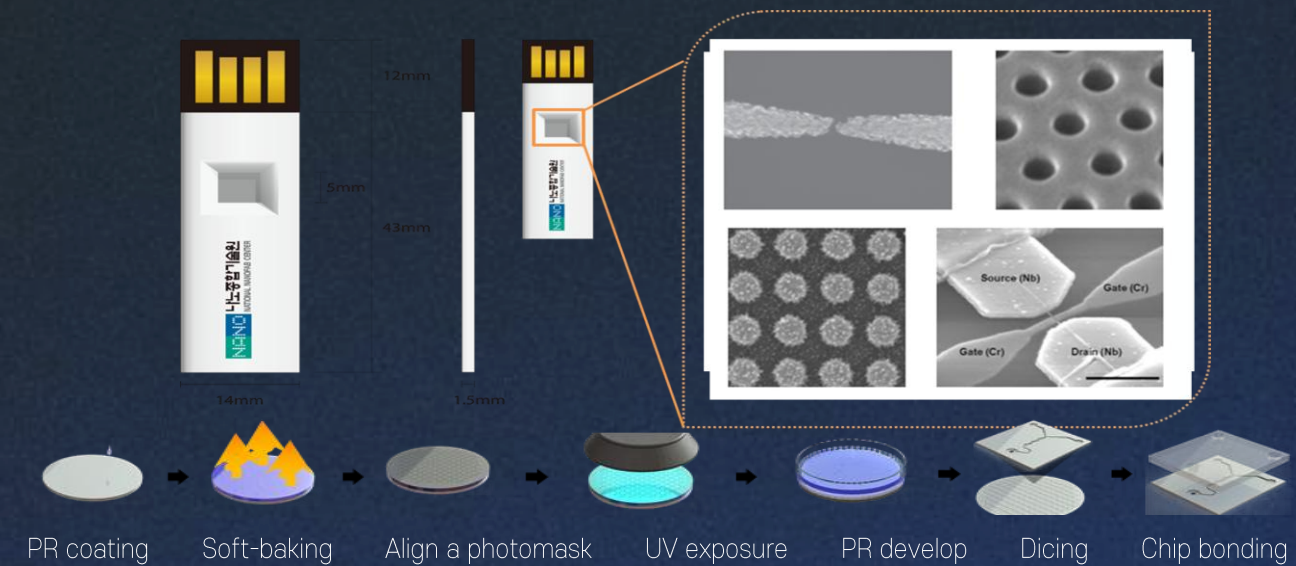
Leading Nanotechnology and Driving Innovation for the Future

03 "What We Offer"

Nano-medical Device Platform

Integration of nanostructures into a USB platform

- Biosensors with nanostructures fabricated using semiconductor processes



- Development of biosensor-based point-of-care devices using semiconductor fabrication technologies

Microfluidic Platform for Drug Delivery Device

- Development of microfluidic devices through bonding of silicon and glass wafers containing micropatterns

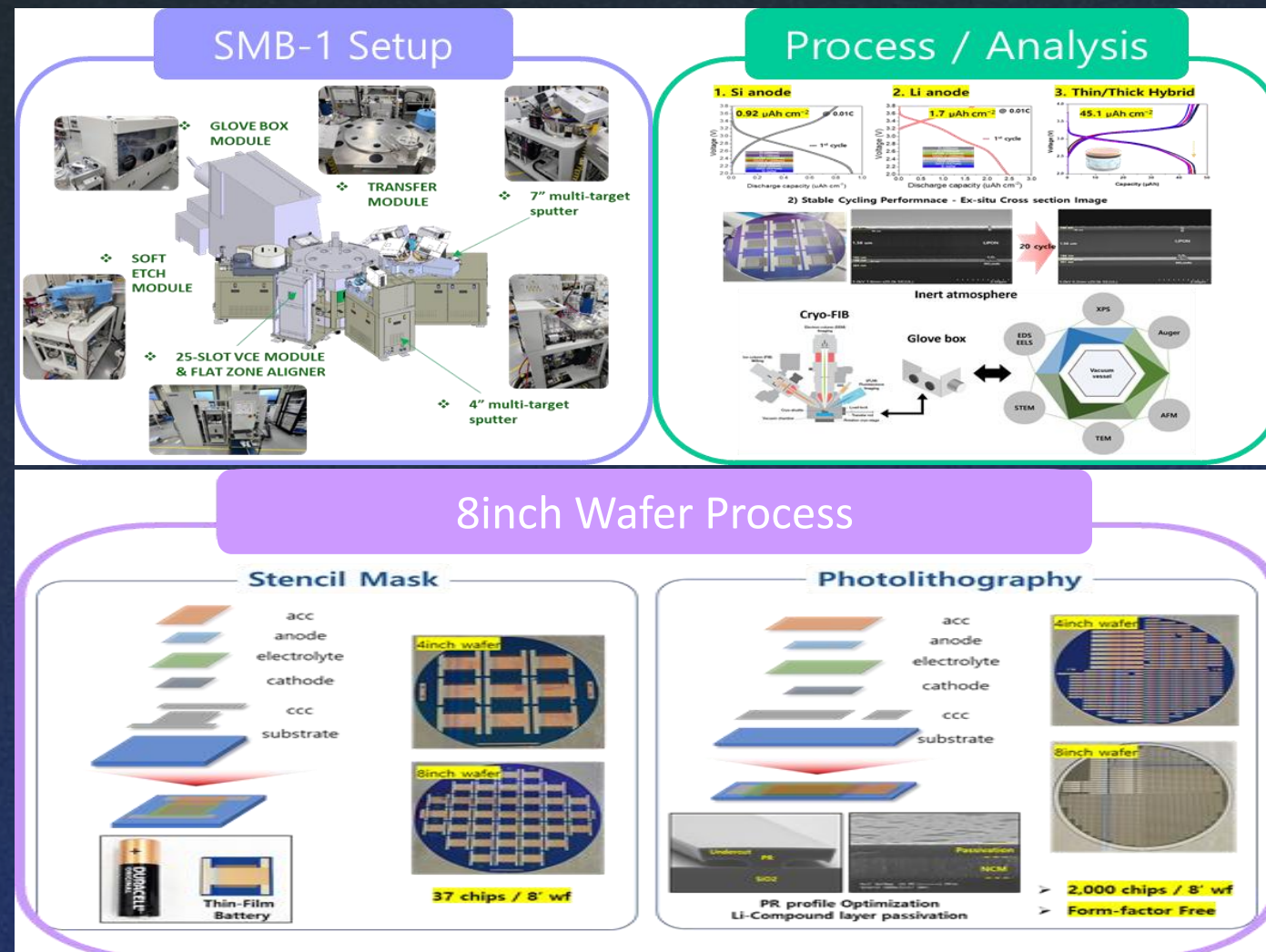


03 "What We Offer"

Nano Device Materials Platform

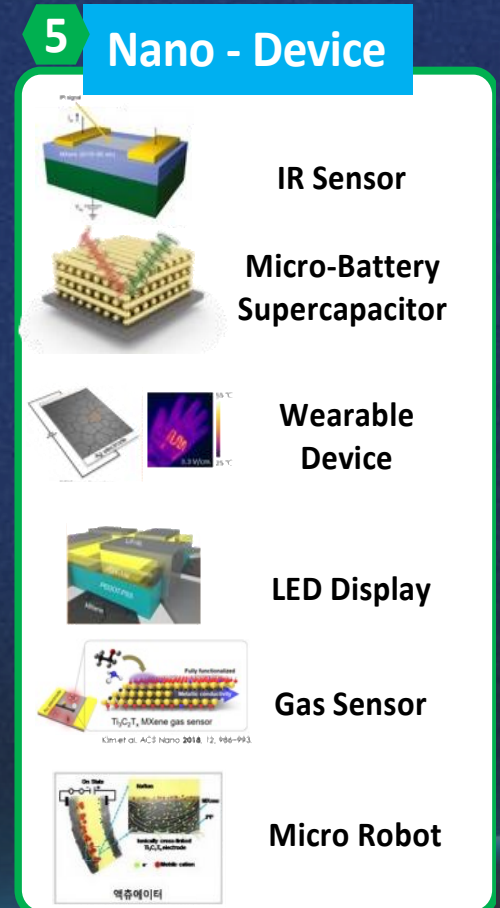
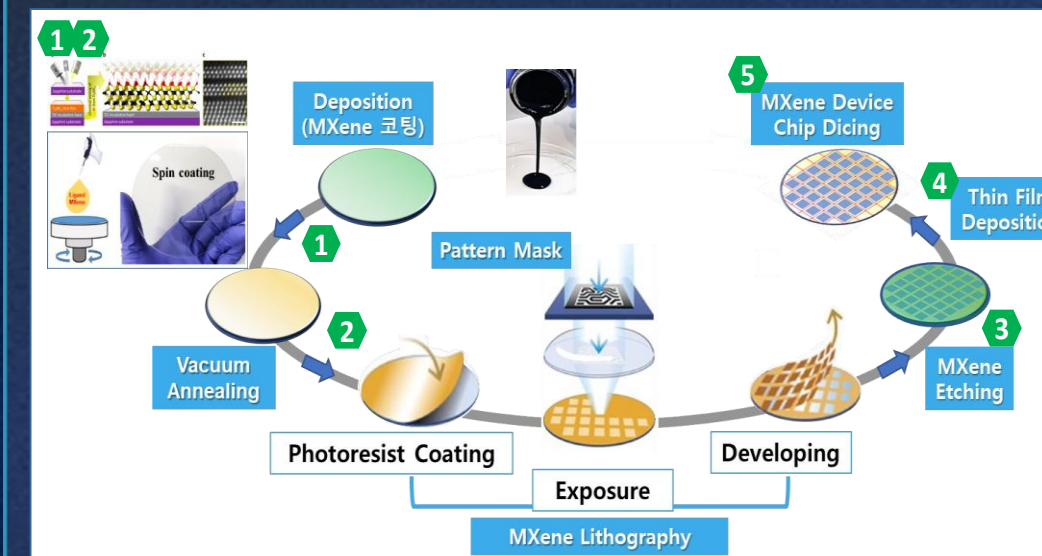
From Li Compound Material to Micro-Battery Devices

Semiconductor-Nano Process



From Nanomaterial to Nano-Device

2D MXene, 2D Graphene(CVD, Coating),
Nano-Fiber(Polymer), Thin Film,
3D Nanostructure(SiO_2 , Si, Polymer, Metal)



03 "What We Offer"

Workforce Development

We provide world-class workforce development programs based on the following strengths:

- #1 : **Hands-on training programs** delivered through cutting-edge FAB infrastructure and XR-based learning equipment
- #2 : **Dynamic coaching and mentoring** led by experts from both industry and academia (internal/external)



Connecting Talent with Opportunity

Comprehensive programs for educations, skills training and workforce development



Training Platform Using XR/Digital Twin

Simulation-based equipment troubleshooting and process optimization training

03

"What We Offer"

Global Collaboration

Europe
(IMEC)

Asia

America
(NY Creates)



Joint R&D Project (NY CREATES, US)

- **Objective**
Supporting International Joint R&D to commercialization core semiconductor technologies in collaboration with NY CREATES and National NanoFab Center
- **Beneficiaries**
Consortia composed of Korean and US researchers, including universities, and government-funded research institutions



Testbed Project (NY CREATES, US)

- **Objective**
Support demonstration and evaluation through the NY CREATES 300mm front-end/back-end infrastructure, including EUV facilities
- **Supported Areas**
Semiconductor materials(e.g. photoresists), Equipment(e.g. test wafer fabrication), Device processing, Advanced packaging
- **Beneficiaries**
Korean companies involved in semiconductor materials, parts, and equipment



Internship Program (imec, Belgium)

- **Objective**
Foster global R&D talent by supporting internships at leading international semiconductor R&D institutions
- **Beneficiaries**
Graduate students (Master's or Ph.D level) in Korea
* A total 24 students were selected for 2024-2025
- **Scope of support**
Operational costs for conducting internship program

04

Future Direction

Vision

Global Leader in Nano-Semiconductor R&D Support
NNFC, We **"Represent"** Korea

Strategy

Building Nano-Semiconductor
Ecosystem

Service Provider

Driving
Global Growth

Ensuring Safety
First

❖ **Enhancing collaboration and cooperation** between domestic and international public semiconductor facilities and the private sectors

❖ **Upgrading in-house capabilities** to keep up with future technologies such as advanced packing technology, quantum sensor technology and AI

❖ **Maintaining sustainability** with 'safety first' principle and improving energy efficiency while following green chemistry principles

12-inch
Materials &
Parts &
Equipment
Testbed

12-inch
Advanced
Packaging
Testbed

Nano-Semiconductor
Convergence
Platform

Next Generation
Neuromorphic
Semiconductor

Global
Collaboration

NNFC,
We Are Always Here for
Your Success

Nano-semiconductor R&D Service Provider,
NNFC, We "Represent" Korea

Thank you